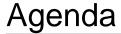


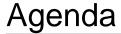
We drive efficiency in drives Our expertise for your optimal drive systems







- 1 Introduction
- A closer look on inverter solutions
- Product solutions overview
- 4 Efficient solutions with IGBT7 and Silicon Carbide MOSFETs
- 5 Key take-aways
- 6 Further information and links





1 Introduction

A closer look on inverter solutions

Product solutions overview

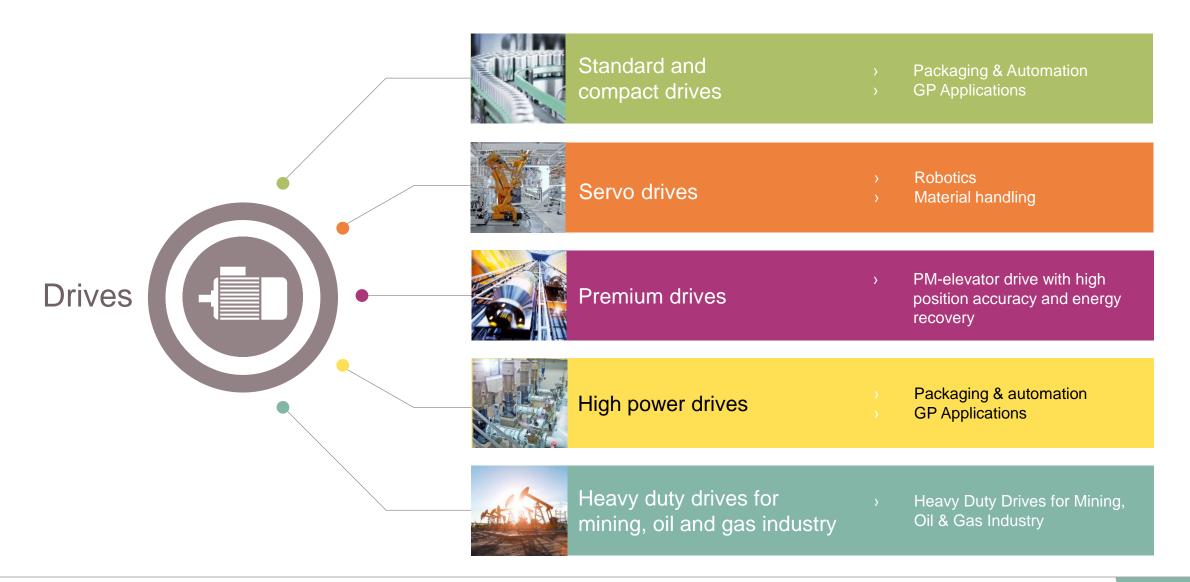
4 Efficient solutions with IGBT7 and Silicon Carbide MOSFETs

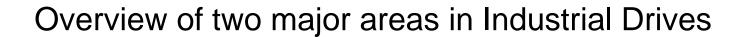
5 Key take-aways

6 Further information and links











Standard and compact drives

370 W 1250 kW

Requirements

- Performance and reliability Good price / performance ratio
- Safety features

Key applications

Pumps and fans

Cranes

Process automation

Marine drives

Infineon products

) iMOTION™

EconoPIM™

CIPOS™ IPM

-) EconoDUAL™
- EiceDRIVER™ gate driver
- > PrimePACK™

EasyPIM™

Servo drives

370 W 315 kW

Requirements

- High positioning accuracy
- Fast response with no overshoot

High reliability

Key applications

Robotics

Machine tools

Material handling

Infineon products

CIPOS™ IPM

EconoPACK™

Discretes

- EasyPACK™
- EiceDRIVER™ gate driver
- EconoDUAL™





Low voltage drives <1kVac

General purpose drives



Standard & compact drives

Pumps & fans
Process automation etc.
Compressed air systems

Premium drives

Cranes
Marine drives etc.





31%

Servo

Robotics

Material handling

Machine tools etc.

Medium voltage drives >1kVac







9%

Oil & gas industry Rolling mills Pumps & fans etc.



% of total drives market by revenue – "Industrial motor control sourcebook 2018"





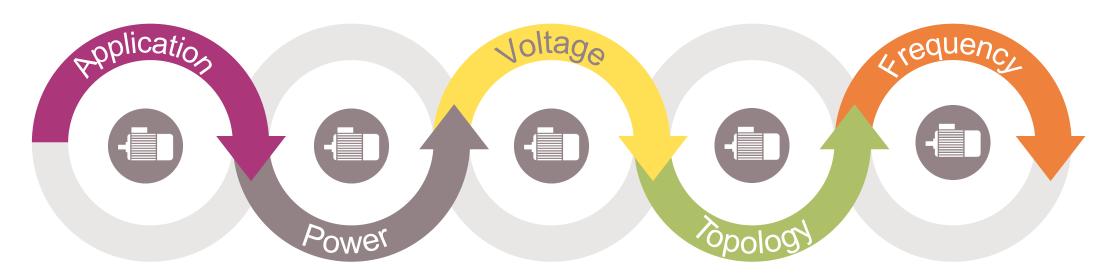
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The five key questions



What is the RMS current/motor power?

What is the topology?



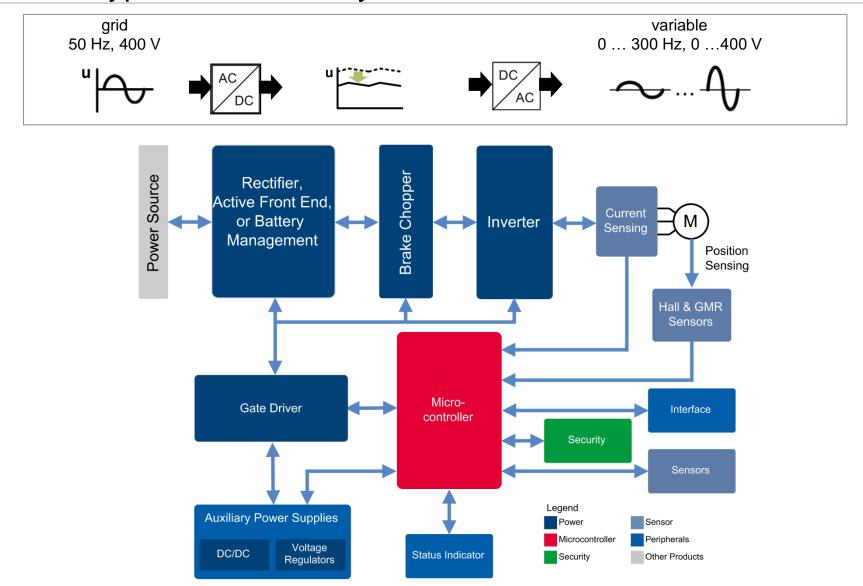
What is your specific application?

What is the voltage AC/DC?

What is the switching frequency?



A closer look to a typical converter system



The levels of integration



Microcontrollers



- XMC[™] controller family based on ARM[®] Cortex[®]-M
- Countless possibilities for motor control

Gate Drivers



- Level shift driver
 - High sideHigh and low sideHalf bridgeThree phase
- Isolated driver (1 & 2 channel)
- Low side driver (1 & 2 channel)

Power Electronics





- Discretes
- > Dual switch
- 3-phase PIM
- Single switch
- Sixpack
- Thyristors & Diode Discs

Intelligent Power Modules

Digital Motor Controller iMOTION™



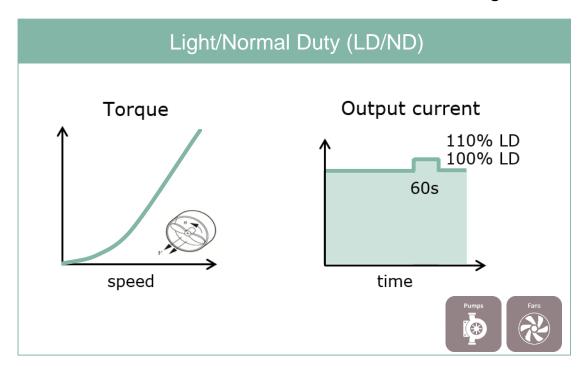
Application requirements for standard, compact and servo drives

	Ctandard and compact drives	Com to drives	ı		
	Standard and compact drives	Servo drives			
Power	Broad portfolio (0.37 1250 kW) 600 V, 1700 V and 1200 V switches (major)	Less broad portfolio (~315 kW or <u>customized current classes</u>) 600 V, 1200 V switches (major)			
f _{sw}	48 kHz <100 kW 24 kHz >100 kW	48 kHz, 16 kHz w/ derating			
dv/dt	≤ 5	kV/μs			
SC	Fast short circuit detection (e.g. 8 µs for IGBT)				
f _{out}	A) Light duty – 50/60 Hz B) Heavy duty 1Hz w/ derating	Low f _{out} common down to 0 Hz (locked rotor)			
OL	A) Light duty e.g. 110% I_N 60 sec 100% I_N 240 sec B) Heavy duty e.g. 150% I_N 60 sec 100% I_N 240 sec	 A) High overload e.g. 200% I_N 3 sec 0% I_N 7 sec B) Very high overload e.g. 300% I_N 0.25 sec 70% I_N 3.75 sec 	300%		

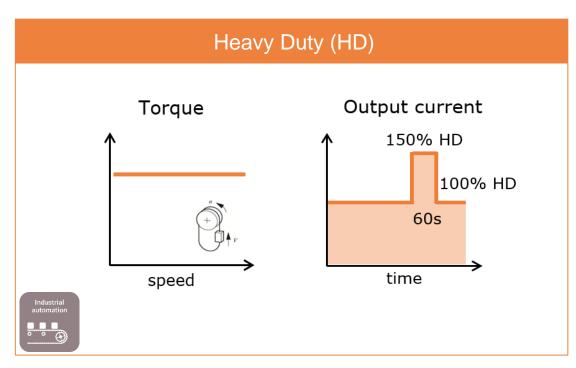


Overload ratings

Overload capability is the property in which, during acceleration operations, the inverter temporarily delivers a higher current than the rated current. There are two sorts of ratings used in industrial drives:

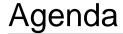


Applied in fans and pumps, since they do not require high torque at low speed and have a 110% overload rating



- Applied in industrial automation and requires high torque at low speeds and a 150% overload rating
- The base load current is reduced when compared to normal duty

For Servo drives the overload capability can increase up to 300% of rated current.





1 Introduction

A closer look on inverter solutions

Product solutions overview

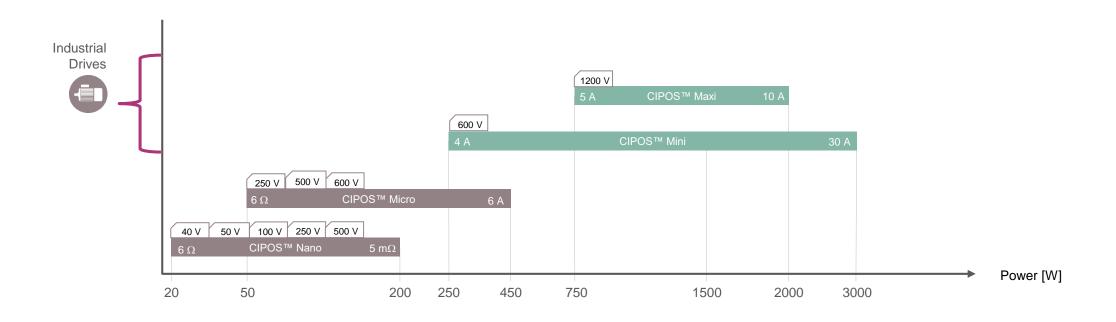
4 Efficient solutions with IGBT7 and Silicon Carbide MOSFETs

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Broad IPM portfolio serving power ranges from 20 W to 3 kW

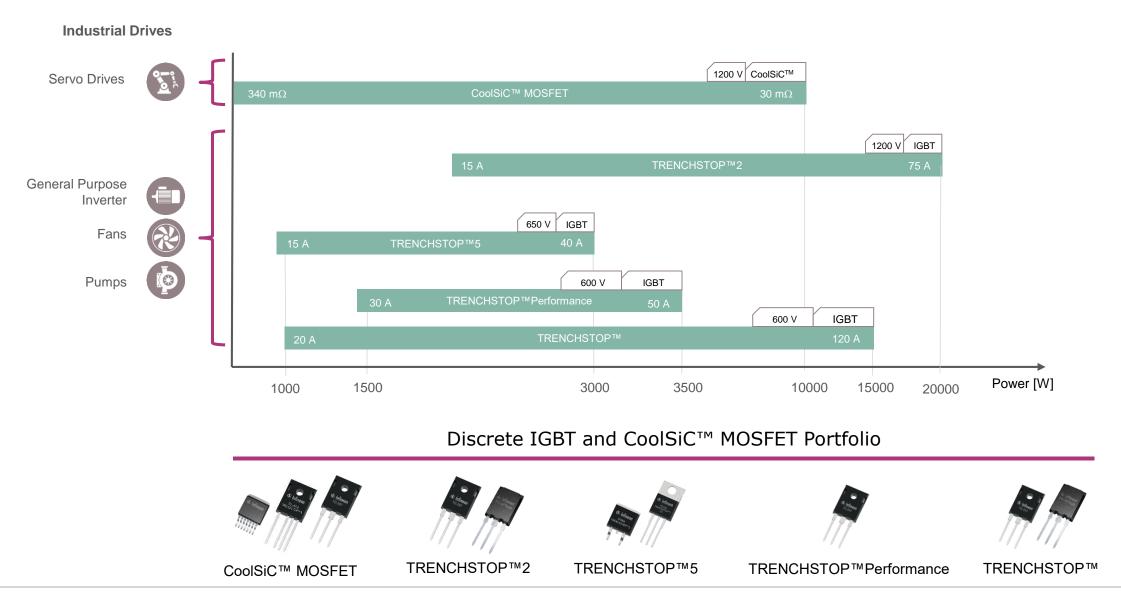


Intelligent Power Module Portfolio



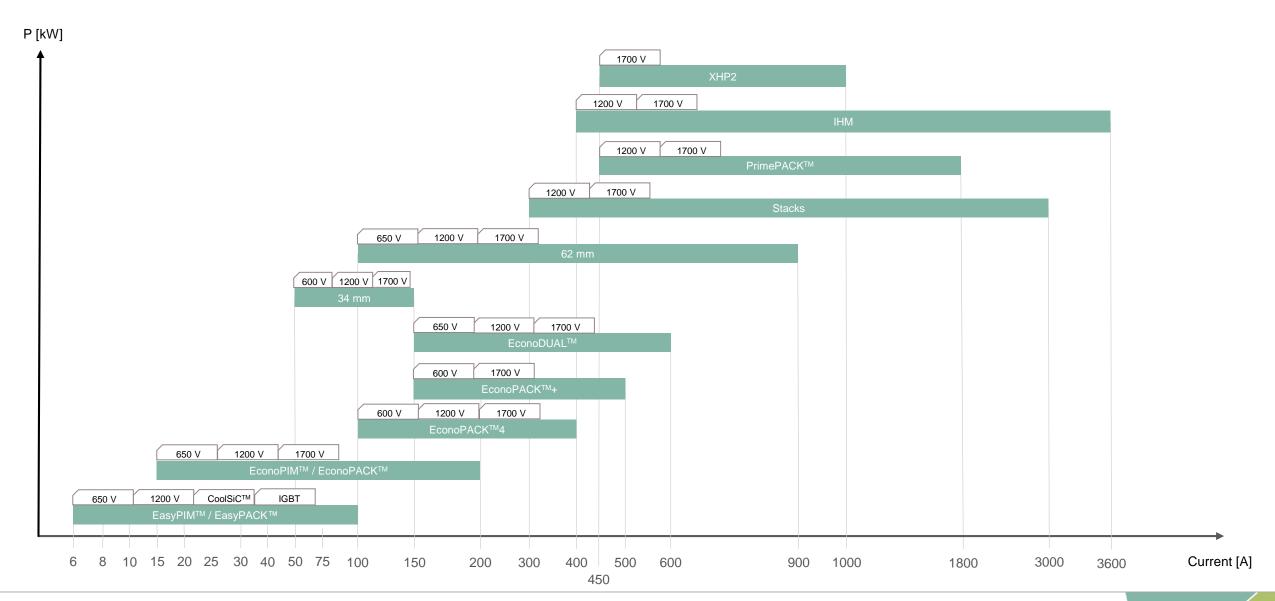


Broad discrete IGBT & SiC portfolio serving power ranges up to 20 kW





Broad IGBT package portfolio serving current ranges from 6 to 3600 A



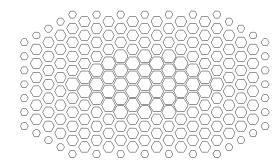




Technical benefits with pre-applied thermal interface material

Features

- Best in class thermal resistance
- Pre-applied to Power Modules
- Dry to the touch
- Fully qualified



Printed pattern

Benefits

- Reduced process time in manufacturing
- Simplified mounting
- Increased system reliability
- Increased system lifetime
- Optimized thermal management
- Improved handling in mounting and maintenance

Product examples

Econo



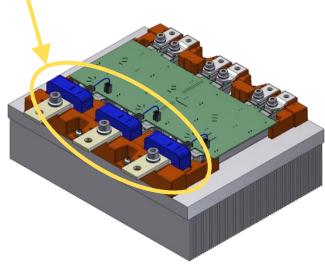
Easy





EconoDUAL™ 3 with integrated shunts – cost reduction by integration

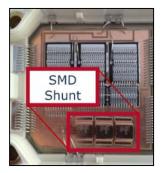
Hall effect current sensor

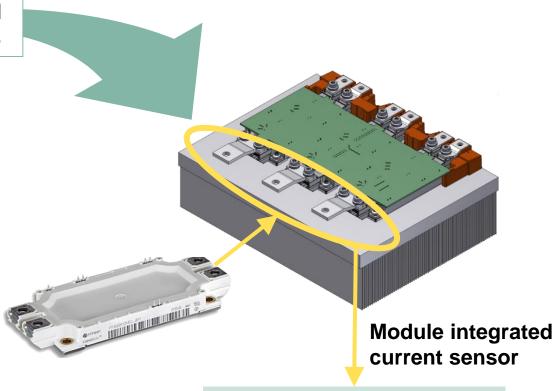


Three phase inverter 240 kW

cost savings due to including shunts

replace external current sensors

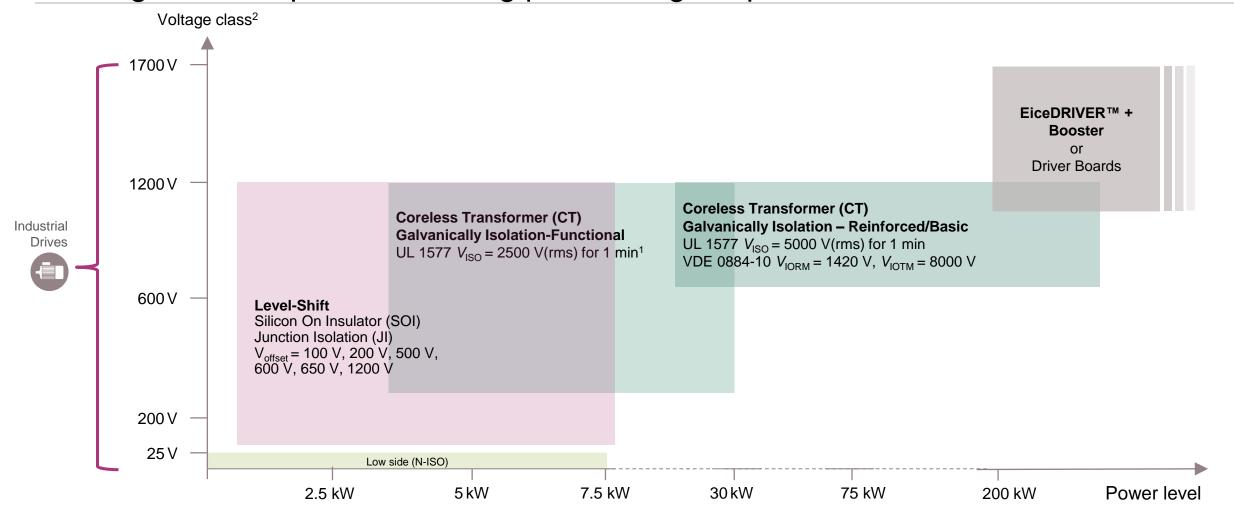




- cost reduction
- reduced space
- reduced cabling effort



Broad gate driver portfolio serving power ranges up to 200 kW and above



Note 1: 1EDC Compact only

Note 2: Voltage class is defined based on different driver configurations.

^{1.} For single high-side, high- and low-side, half bridge and three phase gate drivers, voltage class is defined as switch break down voltage in applications.

^{2.} For low side drivers, voltage class is defined as maximum operating range supply voltage.

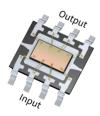
^{5.} For special cases as 1EDNx550 (1EDN-TDI), common mode rejection (CMR) voltage range up to 80 V.



Key gate driver categories for drives

Non-Isolated GD

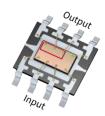
Low Voltage



- Comprehensive Families of single- and dual-low-side drivers with flexible options for output current, logic configurations, and UVLOs
- Rugged technology of the high-voltage gate drivers, and on the latest state-of-the-art 130-nm process
- Industry-standard DSO-8 and small formfactor SOT23 and WSON packages

Level-Shift GD

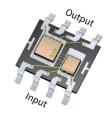
Junction Isolation (JI) & Silicon on Insulator (SOI)



- Proven JI technology trustfully used in all high-voltage gate drive applications for 20 years
- Infineon SOI technology with integrated boot-strap diode, lower level-shift losses, and industry best-in-class robustness against -VS transient spikes
- Largest portfolio of 200 V, 600 V, 700 V and 1200 V industrystandard gate drivers

Isolated GD

Coreless Transformer



- Magnetically-coupled isolation technology provides galvanic isolation for industrial applications
- Strongest gate-drive output currents (up to 10 A) reducing need for external booster circuits
- Reliable and accurate protection options of precise & tight desat protection, active Miller clamp, isolation rating in different packages

Solid-State Relay

Optical Safety Isolation



- Optically isolated technology provides galvanic isolation for safety applications
- Established and reliable products with over 20 years of history
- Wide range of applications from industrial automation to test and measurement equipment



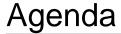
Recommended gate drivers for Drives

Application	Voltage class	Configuration	Part number	Source/Sink current typ.	Packages	Description	Suitable power switches and modules		
	200 V	Half-Bridge	IRS2007S/M	0.29/0.6 A	DSO-8, VQFN- 14	200-V half-bridge with V _{CC} & V _{BS} UVLO	StrongIRFET™ (IRF135B203, IRF135SA204) OptiMOSTM 3 (IPB072N15N3, IPB042N10N3 G, IPB107N20N3)		
		High and Low Side	2ED2106S06F	0.29/0.7 A	DSO-8, DSO-14				
	650 V	Half-Bridge	2ED2304S06F	0.36/0.7 A	DSO-8	Infineon SOI technology with integrated bootstrap diode			
		Half-Bridge	2ED2184S06F	2.5/2.5 A	DSO-8, DSO-14		TRENCHSTOP™ IGBT+Diode (IKD10N60RF, IKA15N65ET6, IKW30N60DTP, IKB40N65ES5)		
		Half-Bridge	2EDL23I06PJ	2.3/2.8 A	DSO-14	Infineon SOI technology with integrated bootstrap diode, OCP, EN, FAULT-RPT, SD-ACT	EasyPIM™ 1B/2B module (FP10R06W1E3_B11,FP15R06W1E3_B11, FB20R06W1E3,		
Inverter	600 V	Single High-Side	IRS2127S	0.29/0.6 A	DSO-8	FAULT-RPT, OCP	FP20R06W1E3_B11, FB30R06W1E3) EasyPACK™ 1B module (FS20R06W1E3_B11)		
(<3.5 kW)	600 V	High and Low Side	IRS2186(4)S	4/4 A	DSO-14, DSO-8	600-V high and low side driver with high current			
		Three-Phase	6EDL04I06PT	0.165/0.375 A	DSO-28 300 mil	Infineon SOI technology with integrated bootstrap diode, OCP, EN, FAULT-RPT			
	1200 V	Half-Bridge	IR2214SS	2/3 A	SSOP-24	1200-V half-bridge driver with DESAT, Synchronization, SD-SOFT, FAULT-RPT	TRENCHSTOP™ IGBT+Diode (IKW25N120T2, IKW40N120T2, IKQ75N120CT2) EasyPIM™ 1B/2B module (FP15R12W1T4_B11, FP15R12W2T4) EasyPACK™ 1B/2B module (FS25R12W1T4_B11) Easy 1B/2B 3-Level module (F3L15R12W2H3_B27) EconoPIM™ 2 module (FP25R12KT4_B15)		
		Three-Phase	6ED2230S12T	0.35/0.65 A	DSO-24	Infineon 1200-V SOI technology with integrated BSD, OCP (±5%), EN, FAULT-RPT	TRENCHSTOP™ IGBT+Diode (IKW08T120, IKW15N120T2) EasyPIM™ 1B/2B module (FP15R12W1T4, FP15R12W1T4_B11, FP15R12W2T4)		
		Single High-Side	1EDC20I12AH	4/3.5 A	DSO-8 300 mil	Functional isolation, ≥ 100 kV/µs CMTI, short circuit clamping, V _{ISO} = 2500 V(rms) for 1 min (1EDC only), active Miller clamp (MH/MF only), separate sink/source output (AH only)	CoolSiC™ SiC MOSFET (IMZ120R045M1, IMZ120R080M1 - 4-pin)		
Inverter (<7.5 kW)			1EDC30I12MH	5.9/6.2 A	DSO-8 300 mil		TRENCHSTOP™ IGBT+Diode (IKW40N120T2, IKQ50N120CT2, IKQ75N120CT2) EasyPIM™ 1B/2B module (FP25R12W2T4_B11, FP35R12W2T4_B11) EasyPACK™ 1B module (FS25R12W1T4_B11, FS50R12W2T4_B11) Easy 1B/2B 3-level (F3L15R12W2H3_B27)		
	4000.1/		1EDI30I12MF	5.9/6.2 A	DSO-8		EconoPIM™ 2 module (FP25R12KT4_B15, FP50R12KT4G_B15) EconoPACK™ 2/3 module (FS50R12KT4_B15)		
	1200 V	Three-Phase	6ED2230S12T	0.35/0.65 A	DSO-24	Infineon 1200-V SOI technology with integrated bootstrap diode, OCP (±5%), EN, FAULT-RPT	TRENCHSTOP™ IGBT+Diode (IKW40N120T2) EasyPIM™ 1B/2B module (FP15R12W1T4, FP15R12W1T4_B11, FP15R12W2T4)		
		Half-Bridge	2ED020l12-FI	1.5/2.5 A	DSO-18	Functional Isolation on high side, comparator, OPAMP, SD	TRENCHSTOP™ IGBT+Diode (IKW40N120T2, IKQ50N120CT2, IKQ75N120CT2) EasyPIM™ 1B/2B module (FP15R12W1T4_B11, FP15R12W2T4, FP25R12W2T4_B11) EasyPACK™ 1B module (FS25R12W1T4_B11) Easy 1B/2B 3-level (F3L15R12W2H3_B27)		



Recommended gate drivers for Drives

Application	Voltage class	Configuration	Part number	Source/Sink current typ.	Packages	Description	Suitable power switches and modules								
	1200 V	Single High-Side	1ED020l12-F2	2/2 A	DSO-16 300mil	Functional isolation, ≥ 100 kV/µs CMTI, active Miller clamp,	CoolSiC™ SiC MOSFET (IMZ120R045M1, IMZ120R080M1 – 4-pin) EasyPIM™ 1B/2B module (FP15R12W1T4 B11, FP25R12W2T4 B11)								
Inverter (<30 kW)		Dual High-Side	2ED020l12-F2	2/2 A	DSO-36	DESAT, short circuit clamping, FAULT-RST									
		Single High-Side	1ED020I12-BT	2/2 A	DSO-16 300mil	Basic isolation, VDE 0884-10 certified, V_{IORM} = 1420 V, VIOTM = 6000 V; UL 1577 certified, VISO = 3750 V(rms) for 1 min, \geq 100 kV/ μ s CMTI, active Miller clamp, DESAT, short circuit clamping, two level turn off, FAULT-RST	EasyPACK™ 1B module (FS25R12W1T4_B11, FS50R12W2T4_B11) EconoPIM™ 2 module (FP25R12KT4_B15, FP50R12KT4G_B15) EconoPACK™ 2/3 module (FS50R12KT4_B15)								
			1EDI60I12AF	10/9.4 A	DSO-8	Functional isolation, ≥ 100 kV/µs CMTI, Separate sink/source output, short circuit clamping, 125-ns propagation delay	CoolSiC™ SiC MOSFET module (FF11MR12W1M1_B11; FF23MR12W1M1_B11) EconoPIM™ 2/3 module (FP150R12KT4(P)_B11) EconoPACK™ 2/3/4 module (FS150R12KT4(P)_B11) EconoDUAL™ 3 module (FF300R12ME4_B11) EconoPack™+ module (FS300R12OE4, FS450R12OE4) 34 mm module (FF15012RT4) 62 mm module (FF300R12KE4)								
Inverter (<200 kW)	1200 V	Single High-Side	1EDS20I12SV	SRC/2 A	DSO-36	Reinforced isolation, VDE 0884-10, VIORM = 1420 V, VIOTM = 8000 V; UL 1577; VISO = 5000 V(rms); soft shutdown, DESAT, FAULT-RPT, OCP, slew rate control, TLTO	CoolSiC™ SiC MOSFET module (FF11MR12W1M1_B11; FF23MR12W1M1_B11) EasyPACK™ 1B module (FS50R12W2T4_B11, FS75R12W2T4_B11)								
			1ED020l12-B2	2/2 A	DSO-16 300mil	Basic isolation, VDE 0884-10 certified, VIORM = 1420 V, VIOTM = 6000 V; UL 1577 certified, VISO = 3750 V(rms) for 1 min, ≥ 100 kV/µs CMTI, active Miller clamp, DESAT, short circuit clamping, FAULT-RST, TLTO	Easy 1B/2B 3-level (FS3L50R07W2H3F_B11, F3L75R12W1H3_B11, F3L100R12W2H3_B11) EconoPIM™ 2/3 module (FP75R12KT4_B15, FP100R12KT4(P)_B11) EconoPACK™ 2/3/4 module (FS75R12KT4_B15, FS100R12KT4G(P)_B11) 34 mm module (FF50R12RT4, FF100R12RT4)								
		Single Low-Side	1ED44176N01F	0.8/1.75 A	DSO-8	Low-side gate driver with integrated overcurrent protection (±5%), fault reporting, and enable functionality	TRENCHSTOP™ IGBT+Diode (IKW30N65H5, IKW40N65WR5, IKFW40N60DH3E, IKFW50N60DH3E)								
PFC	25 V		IRS44273L	1.5/1.5 A	SOT23-5	Low-side gate driver in small, easy-to-use package	Rapid Diode (IDW30E65D1, IDW60C65D1) CoolMOS™ MOSFET (IPx60R060P7, IPx60R080P7, IPx60R099P7,								
		Dual Low-Side	IRS4427S	2.3/3.3 A	DSO-8	Industry proven dual-low-side gate driver	IPx60R120P7, IPx60R180P7, IPx60R280P7, IPx60R360P7) CIPOS™ Mini (IFCM15S60GD, IFCM10P60GD, IFCM10S60GD)								
01100	650 V	Half-Bridge	2ED2184S06F	2.5/2.5 A	DSO-8, DSO-14	Infineon SOI technology with integrated bootstrap diode	TRENCHSTOP™ IGBT+Diode (IKW30N65F5, IKB40N65EF5)								
SMPS (<3 kW)	600 V	High and Low Side	IRS2186(4)S	4/4 A	DSO-14, DSO-8	600-V high and low side driver with high current	CoolMOS™ MOSFET (IPx60R060P7, IPx60R080P7, IPx60R099P7, IPx60R180P7, IPx60R280P7, IPx60R360P7, IP(W/Z)65R019C7, IP(W/Z)65R045C7, IP(W/Z)65R065C7, IP(W/Z)65R095C7, IPW65R190C7)								
	25 V	Single Low-Side	IRS44273L	1.5/1.5 A	SOT23-5	Non-inverting single low-side driver with CMOS inputs									
Brake Chopper (<3.5 kW)	4000 17		1EDI05I12AF	1.3/0.9 A	DSO-8	Functional isolation, ≥ 100 kV/µs CMTI, short circuit clamping,	TRENCHSTOP™ IGBT+Diode (IKW40N120T2, IKQ50N120CT2, IKQ75N120CT2)								
120	1200 V S	1200 V	1200 V	1200 V	1200 V	1200 V	1200 V	1200 V	1200 V S	200 V Single High-Side	1EDI10I12MF	2.2/2.3 A	DSO-8	separate sink/source output (AF only), active Miller clamp (MF only)	IIIQ/ONIZOO1Z)





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Easy with TRENCHSTOP™ IGBT7 brings multiple benefits



Tailored for Drives Application

We focus on customer's application needs: From Product thinking to System understanding



Time to Market

One change at one time: All improvements realized on chip level



Proven Quality

We bring chip innovation in mature and known housing technology



Scalability for Platform Design

> Easy hits the 100: Easy 1B, 2B from 10 A up to 100 A



Lower System Cost

 Easy with IGBT7 portfolio is designed for system cost optimization



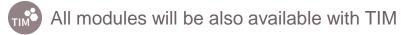
Easy with TRENCHSTOP™ IGBT7 portfolio

Package			10 A	15 A	25 A	35 A	50 A	75 A	100 A
ΔIA	EasyPIM™ 1B				*				
	EasyPIM™ 2B						*		
6-pack	EasyPACK™ 1B						*		
	EasyPACK™ 2B								*











Features of the TRENCHSTOP™ IGBT7 chip



Optimized for simple driving

Higher power density and frame size jump

Lower on state voltage $V_{CE(sat)}$ and V_f

TRENCHSTOP™ IGBT7

Improved free wheeling diode softness

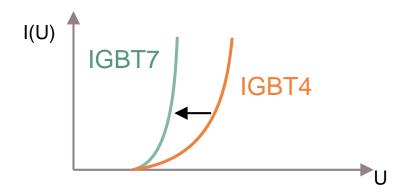
Overload Capability at T_{vj,op}=175°C

Enhanced controllability of dv/dt

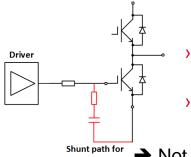


Technical benefits of TRENCHSTOP™ IGBT7

Best-in-class V_{CE,sat}



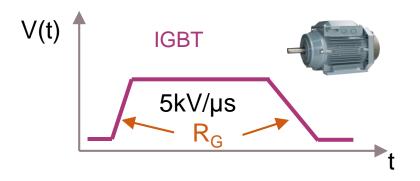
IGBT7 is designed for zero voltage turn-off



- The ratio of input capacitor is optimized to avoid parasitic turn-on
- Gate driver circuit can thus be simplified

→ Not necessary for IGBT7

Enhanced controllability of dv/dt optimized for drive applications



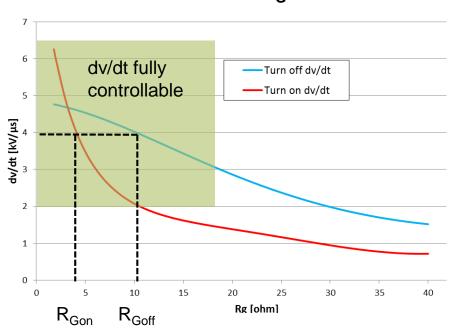
Higher power density with same power in 35% smaller package

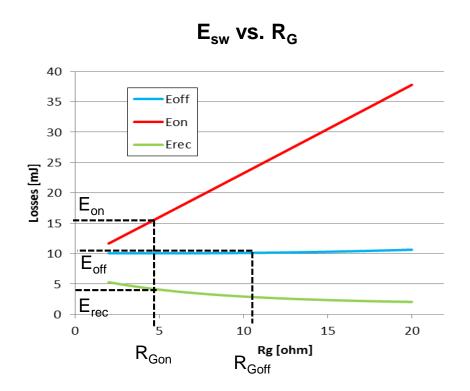






dv/dt vs. R_G







Full control of turn on and turn off dv/dt in range of 2-8kV/µs.



Easy to choose the right gate resistor for specified dv/dt.



Benefits of IGBT7 solutions



Technology Benefits

- Low losses, new chip technology shows extremely lower losses with optimized low V_{cesat}
- dv/dt optimized for 2-8 kV/µs, tailored for drive application
- Short circuit is tailored for better performance, 8 µs @150°C is enough for drive application

- **Simpler gate drive,** is optimized for application condition, only a gate resistor is enough to control
- Increase of T_{vjop} up to 175°C higher power density possible

Customer Benefits

Plug and play

- Pin to pin compatibility with IGBT4 module
- Lower losses
- Higher robustness

Package Jump

- Cost saving on module side
- Compact inverter design
- Higher flexibility on inverter frame size

Reduction of heatsink

- System cost saving
- Compact inverter design

Broad portfolio

- Will be available in a broad power range
- High volume production

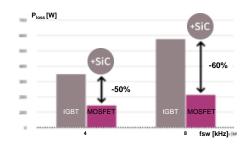


Benefits with SiC solutions



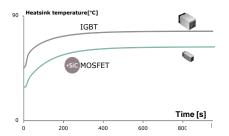
Increased performance

- Reduction of power losses lead to higher performance
- 60% reduction @ 8 kHz compared to IGBTbased



Higher robustness

- 10 K lower operating temperature of heatsink
- Cooling efforts significantly reduced



Higher power density & lower system cost

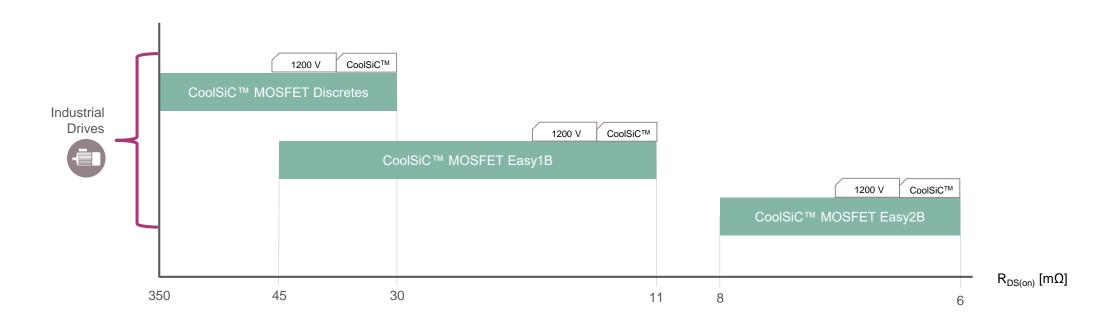
- Heatsink can be reduced by 2/3 compared to IGBT
- Leads to a much higher system power density



Note: Measurements based on drive demonstrator (22 kW; 50 Hz output freq.; dv/dt <5 kV/µs; IGBT system under same conditions)



1200 V SiC-MOSFET portfolio for Easy and discrete

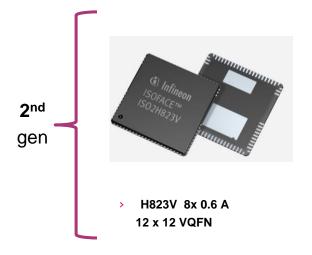


Easy and discrete portfolio



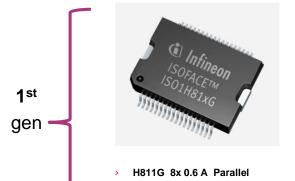


ISOFACE™ product family – Galvanic isolation & diagnostics integrated



8-channel switch IC

- 2.5 kV galvanic isolation
- > 3.3 V μC interface (SPI, parallel)
- Diagnostics per channel:
 - Open load
 - Short to V_{bb}
 - Short to GND & overload
 - Over temperature
- 5-fold global diagnostics



H812G 8x 0.6 A SPI H815G 8x 1.2 A Parallel

H816G 8x 1.2 A SPI

8-channel switch ICs

- Integrated galvanic isolation
- > Direct interface to μC
 - 3.3 V/5 V
 - Serial or parallel
- > Short-circuit protection
- > Inductive load switching
- > Up to 1.2 A load current
- > Integrated diagnostics:
 - Overload & short circuit



XMC1xxx XMC4xxx

8-ch. digital input ICs

- > Integrated galvanic isolation
- Direct interface to μC
 - 3.3 V/5 V

ISO1H81xG

- Serial or parallel
- > IEC-input types: 1/2/3

		Sampling speed	Filter settings	Diagno V _{bb} -monitor		
>	I811T	125 kHz	4 / IC			
>	1813T	500 kHz	9 / channe	·	✓	

8-channel switch ICs

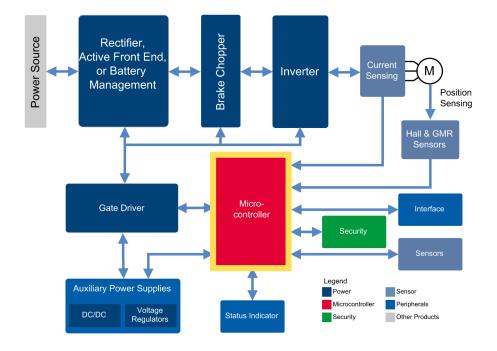
8-channel input ICs





Tasks of the controller

- IGBT control (PWM generation)
- Motor feedback sensing (current, position, speed)
- Speed, torque and position control
- Communication (industrial Ethernet, CAN...)



Solutions for industrial drives

- 32-bit ARM® Cortex™-M0 based XMC1000 family low end
- 32-bit ARM[®] Cortex[™]-M4F based XMC4000 family mid range
- 32-bit TriCore[™] family high end

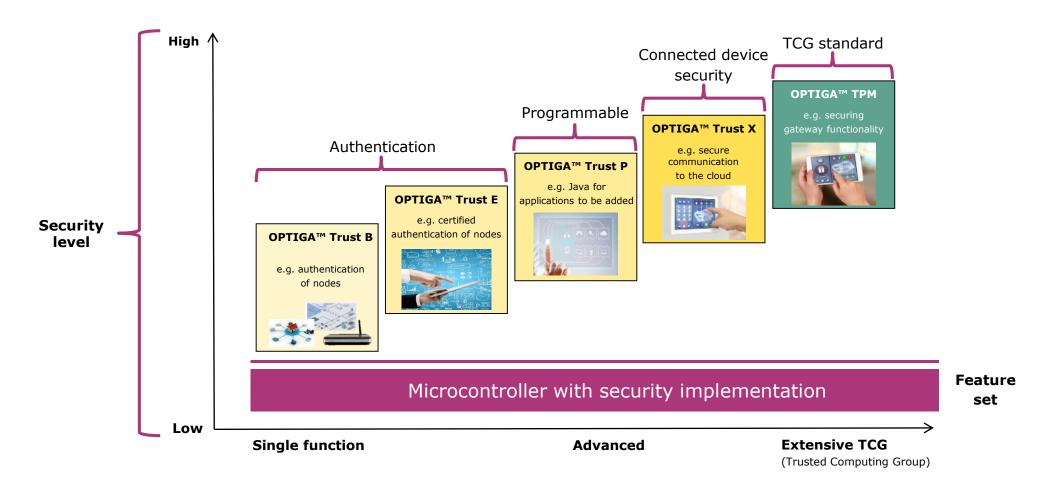








Optimized OPTIGA™ product portfolio to meet security requirements







- 1 Introduction
- A closer look on inverter solutions
- Product solutions overview
- 4 Efficient solutions with IGBT7 and Silicon Carbide MOSFETs
- 5 Key take-aways
- 6 Further information and links



Key take-aways



Nearly 50% of the world wide consumed electrical energy is use for industrial drive systems

- Mayor applications are pumps, fans and compressors
- High energy saving is possible with process optimization enabled by speed and torque control of the motor drive systems for electrical motors

Infineon offers optimized technologies

- > IGBT7 perfectly matched to the needs of drives applications like overload and switching speed control
- > SiC-MOSFETs enabling a high degree of integration due to low losses

Infineon has a unique one shop offering for industrial drives

- The right fit package for the inverter in power range from W with IPM's and 100's of kW with EconoDUAL™
- Gate Driver solutions with enhanced functionalities
- Current sense solutions
- > Peripherals like industrial interface IC's, security solutions and microcontrollers

Infineon is the right partner for customized solution and high volume products

With outstanding quality standards and production capability





1 Introduction

A closer look on inverter solutions

Product solutions overview

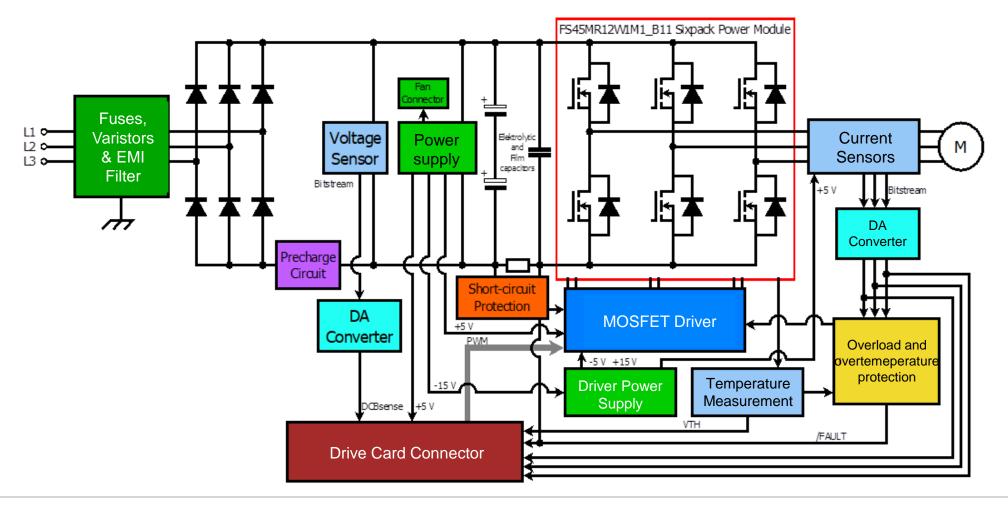
- 4 Efficient solutions with IGBT7 and Silicon Carbide MOSFETs
- 5 Key take-aways

6 Further information and links

Modular Application Design Kit (MADK) CoolSiC™ MOSFET evaluation board for industrial drives



- > Compact and flexible 3-phase motor drive evaluation platform
 - CoolSiC™ MOSFET in EasyPACK™ 1B can easily tested



Modular Application Design Kit (MADK) CoolSiC™ MOSFET evaluation board for industrial drives



Parameters	Values	Conditions / Comments		
Inc	luding <u>FS45MR12W1M1_B11</u> & <u>1EDI20H12AH</u>			
Input				
Voltage	$340-480\;V_{rms}$			
Current	16 A _{rms}	Input 400 V _{AC} , Ta = 25 °C		
DC bus voltage	530 V – 670 V typ.			
Switching frequency	18 kHz nom 100 kHz max			
Output				
3ph P _{out} with mains line choke	11 kW max	Input 400 V_{AC} , f_{sw} = 18 kHz, T_a = 25 °C, T_h = 70 °C, forced convection cooling		
3ph P _{out} without mains line choke	6 kW	Input 400 V_{AC} , f_{sw} = 18 kHz, T_a = 25 °C, T_h = 70 °C, forced convection cooling, limited by input current		
Current per leg at f _{sw_nom}	16 A _{rms}	Input 400 V_{AC} , $f_{sw} = 18$ kHz, $T_a = 25$ °C, $T_h = 70$ °C, forced convection cooling		
Current per leg at f _{sw_max}	8 A _{rms}	Input 400 V_{AC} , $f_{sw} = 100$ kHz, $T_a = 25$ °C, $T_h = 70$ °C, forced convection cooling		

- 3ph AC-connector, EMI filter, bridge rectifier, inrush current limiter, 3ph voltage source inverter and a 3ph output for connecting the motor
- Isolated current, voltage sensing unit using $\Delta\Sigma$ -ADC (digital/analogue output)
- > Temperature sensing circuitry
- Auxiliary power supply











Product page links

) IGBT7

SiC-MOSFET

Gate Driver

Magnetic Current Sensor

Application pages

- Overview
- Induction motor
- Permanent magnet synchronized motor
- Servo motor
- Motor control for industrial automation
- > Robotics





SiC Forum

Join the discussion
About Silicon Carbide





Part of your life. Part of tomorrow.

